

CIR-V4DASW2616G

DDR4 Registered DIMM 2666MHz 16GB

Description

This specification defines the electrical and mechanical requirements for 288 pin, 1.2 V (VDD), Double Data Rate, Synchronous DRAM Dual In-Line Memory Modules.

Reference design examples are included which provide an initial basis for DDR4 R-DIMM designs. Modifications to these reference designs may be required to meet all system timing, signal integrity and thermal requirements for DDR4-2666 support.

Specifications

Density	16GB
Pin Count	288pin
Type	Registered
Dimensions	133.35mm x 31.25mm
ECC	with ECC
Component Config	1G x 8 bit
Data Rate	2666 MHz
CAS Latency	19
Voltage	1.2V
PCB Layers	8
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Dual Rank

Features

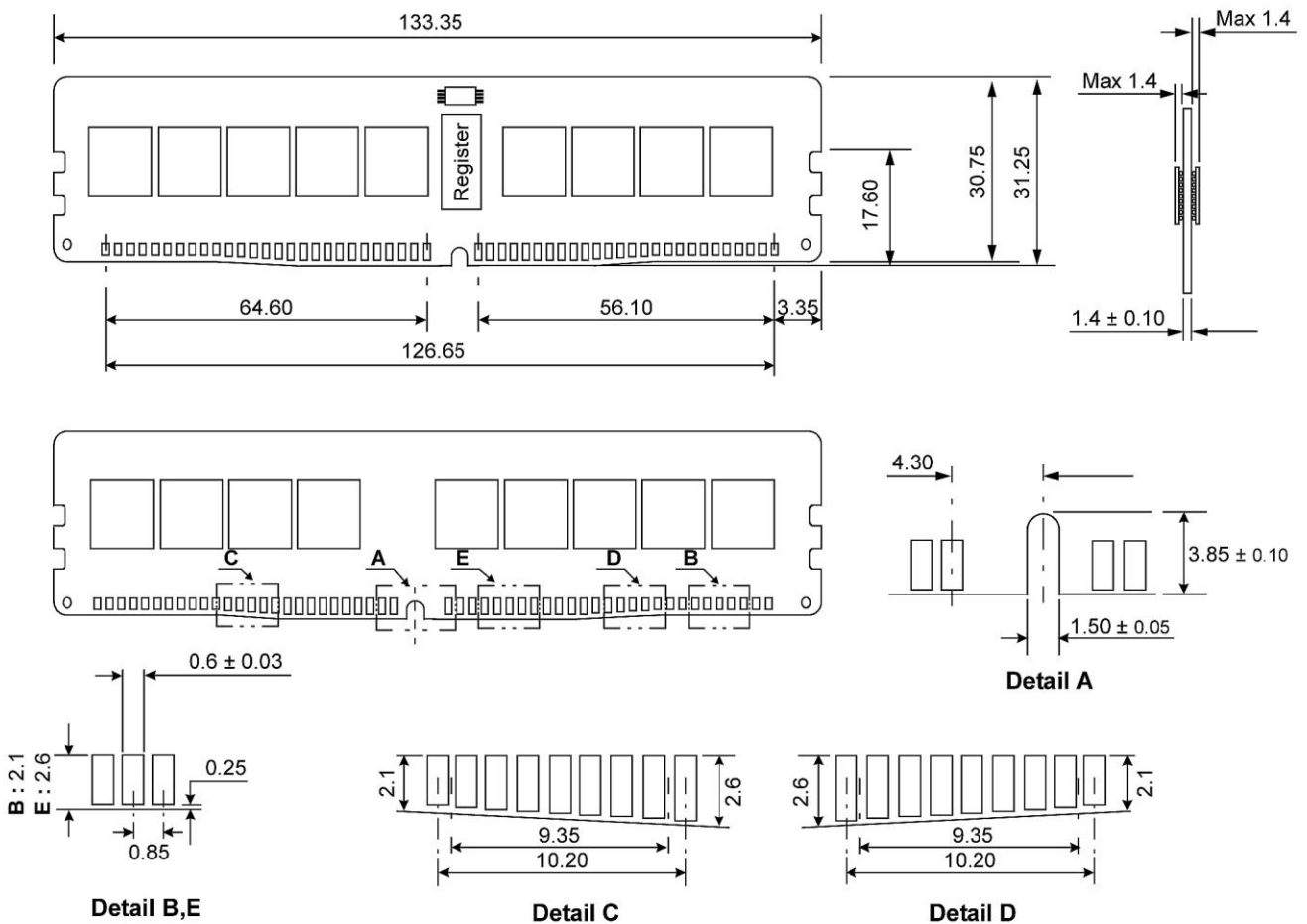
- 288-pin Registered Dual Inline Memory Module (RDIMM)
- Organization: 2Gx72 based on 1Gx8* 18 components / 2 Ranks
- CL-tRCD-tRP : 19-19-19
- JEDEC standard 1.2V (\pm 0.06V) Power Supply
- 16 Banks (4 Bank Groups)
- Programmable CAS Latency: 11,12,13,14,15,16,17,18,19
- Burst Length: 8(Interleave/nibble sequential)
- Bi-directional Differential Data-Strobe
- On Die Termination (ODT)
- Average Refresh Period 7.8us at lower than a TCASE 85°C, 3.9us at 85°C < TCASE < 95 °C
- RoHS Compliant

Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support								CL-tRCD-tRP
		CL11	CL12	CL13	CL14	CL15	CL16	CL17	CL19	
DDR4-2666	PC4-21300	1600	1600	1866	1866	2133	2133	2400	2666	19-19-19

Package Dimensions

Unit: mm



Tolerances : ± 0.15mm unless otherwise specified